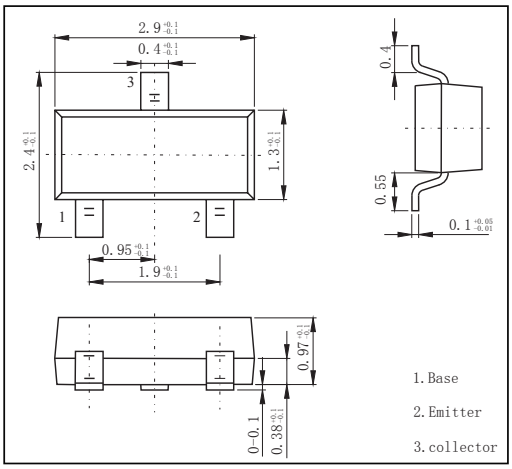
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- High voltage and high current
- VCEO:=-50V(min.),IC=-150mA(max.)
- Low niose: NF=1dB(Typ.) at f=1KHz
- PNP TRANSISTORS
- Collector-Base Voltage: VCBO=-60V

MECHANICAL DATA

- Case style:SOT-23 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-150	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	- 55 ± 150	℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C= -100 uA, I_E=0	-50			V
Collector-emitter breakdown voltage	V_{CEO}	I_C= -0.1mA, I_B=0	-50			V
Emitter-base breakdown voltage	V_{EBO}	I_E= -100 uA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -50V , I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -50V , I_B=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= - 5V , I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}= -6V, I_C= -2mA	130		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -100 mA, I_B= -10mA			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= -100 mA, I_B= -10mA			-1.1	V
Transition frequency	f_T	V_{CE}= -10V, I_C= -1mA,f=30MHz	80			MHz